

APPENDIX

Claim 1 now read as follows.

1. (Twice Amended) A semiconductor device comprising:

a first region where first transistors each having a first gate oxide film of a first thickness is formed;

b1 a second region, adjacent to the first region, where second transistors each having a second gate oxide film of a second thickness are formed;

trench isolation patterns formed selectively within said first and second regions and extending continuously in a first direction; and

a dummy region having a plurality of dummy trench isolation patterns located in said second region, wherein the dummy trench isolation patterns comprise a trench pattern which constitutes a positioning mark and extends in a second direction different from the first direction so as to connect said dummy trench isolation patterns.